

FIG.1

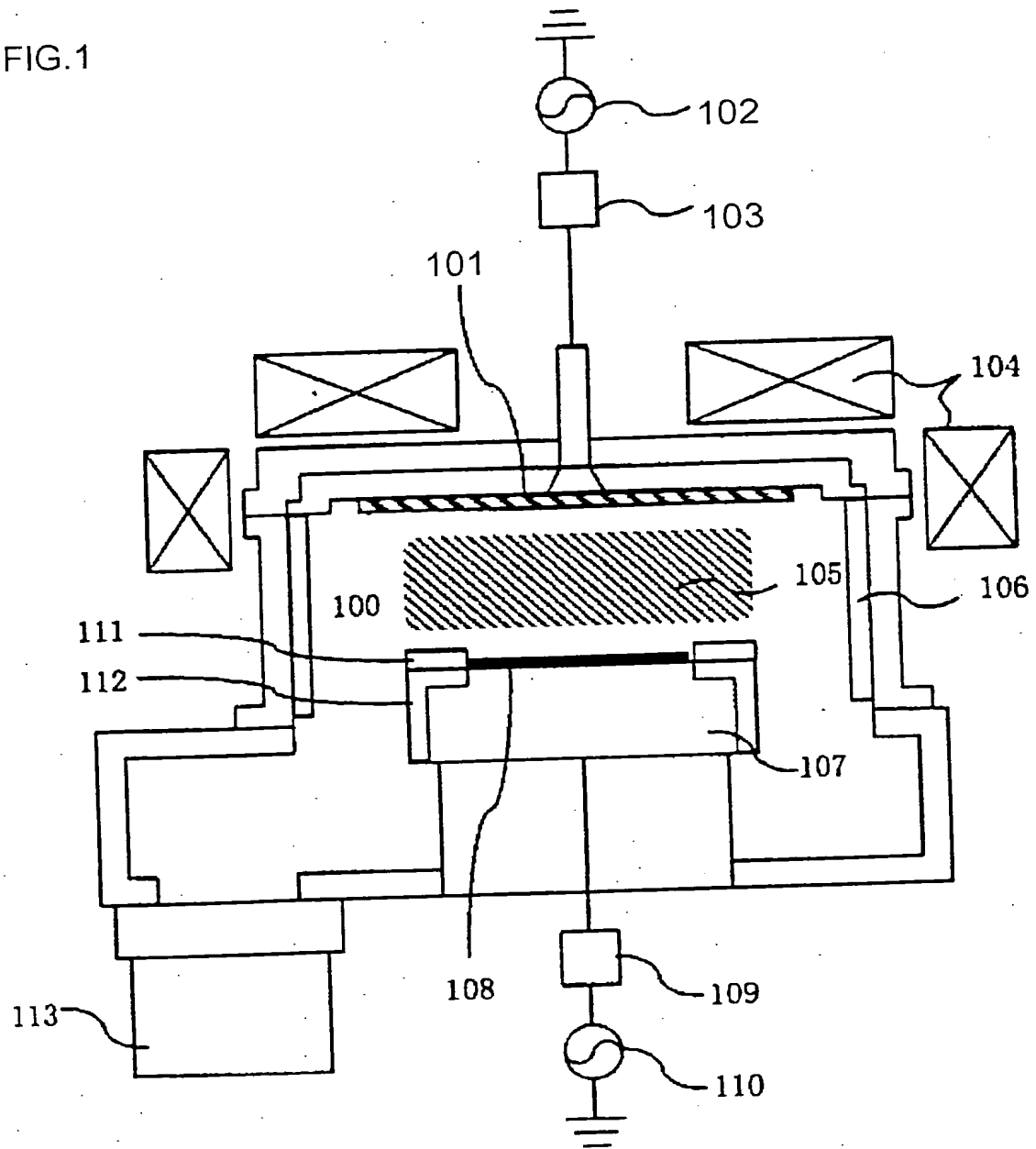


FIG.2

PLASMA SOURCE POWER	1000W
NH ₃ FLOW RATE	125ml/min
PROCESSING PRESSURE	0.5Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.3

PLASMA SOURCE POWER	1000W
NH ₃ FLOW RATE	125ml/min
CO FLOW RATE	50ml/min
PROCESSING PRESSURE	0.7Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.4

PLASMA SOURCE POWER	1000W
NH ₃ FLOW RATE	125ml/min
Ar+CH ₄ FLOW RATE	375ml/min
PROCESSING PRESSURE	2.0Pa
WAFER SUBSTRATE TEMPERATURE	20°C
POWER APPLIED TO SUBSTRATE	850W(8-INCH WAFER)

FIG.5

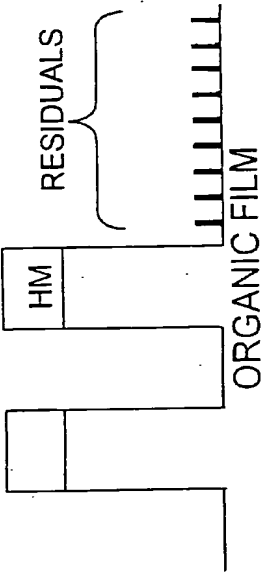
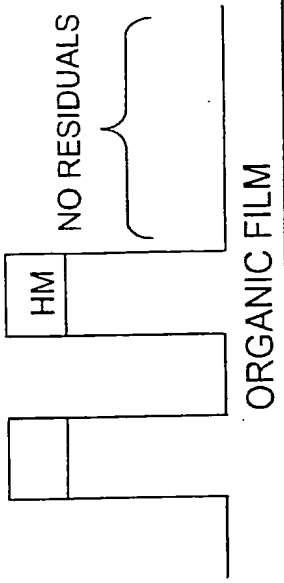
	PRIOR ART	PRESENT INVENTION
ORGANIC FILM ETCHING RATE	488(nm/min)	405(nm/min)
SELECTIVE RATIO TO HM	44(—)	59(—)
NUMBER OF CONTAMINANTS OVER 0.20 μm	224	25
RESIDUALS		

FIG.6

